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Vishay Semiconductors

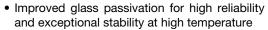
Medium Power Phase Control Thyristors (Stud Version), 25 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	25 A			
V_{DRM}/V_{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V 1200 V			
V_{TM}	1.70 V			
I _{GT}	60 mA			
TJ	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			

Single SCR

FEATURES





• High dl/dt and dV/dt capabilities

- Standard package
- Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- · Medium power switching
- · Phase control applications

	S AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
L		25	Α	
I _{T(AV)}	T _C	85	°C	
I _{T(RMS)}		40	А	
I _{TSM}	50 Hz	420	^	
	60 Hz	440	— A	
2t	50 Hz	867	A2-	
1-1	60 Hz	790	— A ² s	
V _{DRM} /V _{RRM}		100 to 1200	V	
tq	Typical	110	μs	
T _J		-65 to +125	°C	

ELECTRICAL SPECIFICATIONS

Circuit configuration

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT } T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-25RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

Notes

- (1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs
- (2) For voltage pulses with $t_p \le 5$ ms



ABSOLUTE MAXIMUM RAT	INGS					
PARAMETER	SYMBOL		TEST COND	DITIONS	VALUES	UNITS
Maximum average on-state current		190° oinuosi	180° sinusoidal conduction		25	Α
at case temperature	I _{T(AV)}	100 51110501	dai conduction		85	°C
Maximum RMS on-state current	I _{T(RMS)}				40	Α
		t = 10 ms	No voltage		420	
Maximum peak, one-cycle	<u></u>	t = 8.3 ms	reapplied		440	Α
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		350	A
	t = 8.3 ms reapplied Sinusoidal half wave,	370				
Maximum I ² t for fusing	l ² t	t = 10 ms	No voltage	initial $T_J = T_J$ maximum	867	- A ² s
		t = 8.3 ms	reapplied		790	
		t = 10 ms	100 % V _{RRM} reapplied		615	
		t = 8.3 ms			560	
Maximum I ² √t for fusing	l²√t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		8670	A²√s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		0.99	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$, T _J = T _J maximu	ım	1.40	V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), T_J = T_J maximum		10.1	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		5.7	1115.2	
Maximum on-state voltage	V _{TM}	I _{pk} = 79 A, T _J = 25 °C		1.70	V	
Maximum holding current	I _H	T 05 00 and a sel 0 V arial all		/ registive load	130	mA
Latching current	IL	1,1=25 0,8	$T_J = 25$ °C, anode supply 6 V, resistive load		200	1 IIIA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise	$V_{DRM} \leq 800 \; V$	$V_{DRM} \le 800 \text{ V}$ $T_J = T_J \text{ maximum}, V_{DM} = \text{Rated } V_{DRM}$ dI/dt $Gate \text{ pulse} = 20 \text{ V}, 15 \Omega$, $t_0 = 6 \text{ us}, t_r = 0.1 \text{ us}$		180	A/µs
of turned-on current	$V_{DRM} \leq 1000 \; V$	di/dt	Gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum I_{TM} = (2 x rated dI/dt) A	160	Ανμδ
V _{DRM} ≤ 160			,,	150	
Typical turn-on time		t _{gt}	$T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \ \mu s$, $dI/dt = -10 \ A/\mu s$	4	μs
Typical turn-off time		tq	$\begin{split} T_J &= T_J \text{ maximum, } I_{TM} = I_{T(AV)}, t_p > 200 \mu\text{s, } V_R = 100 \text{ V}, \\ dI/dt &= \text{-} 10 \text{ A/}\mu\text{s, } dV/dt = 20 \text{ V/}\mu\text{s linear to 67 } \% \text{ V}_{DRM}, \\ \text{gate bias 0 V to 100 W} \end{split}$	110	μο

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs	
of off-state voltage	uv/di	T _J = T _J maximum linear to 67 % rated V _{DRM}	300 ⁽¹⁾	v/μS	

Note

 $^{^{(1)}}$ Available with: $dV/dt = 1000 \text{ V/}\mu\text{s}$, to complete code add S90 i.e. 25RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P _{GM}			8.0	W
Maximum average gate power	P _{G(AV)}	I j = I j maximum	$T_J = T_J$ maximum		VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
		T _J = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		60	mA
		T _J = 125 °C		35	
	V _{GT}	T _J = - 65 °C		3.0	V
DC gate voltage required to trigger		T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I _{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to +125	°C	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation		K/W	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased	0.35	rv vv	
Allowable mounting toward		Non-lubricated threads	3.4 ^{+ 0 - 10} % (30)	N⋅m	
Allowable mounting torque		Lubricated threads	2.3 ^{+ 0 - 10} % (20)	(lbf · in)	
Approximate weight			14	g	
Approximate weight			0.49	oz.	
Case style		See dimensions - link at the end of datasheet TO-48 (TO-2		-208AA)	

△R _{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.17	0.13		
120°	0.21	0.22		
90°	0.27	0.30	$T_J = T_J$ maximum	K/W
60°	0.40	0.42		
30°	0.69	0.70		

Note

The table above shows the increment of thermal resistance R_{th,JC} when devices operate at different conduction angles than DC

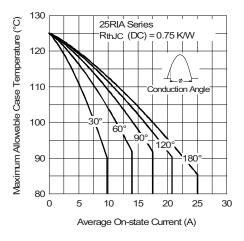


Fig. 1 - Current Ratings Characteristics

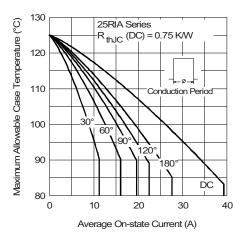


Fig. 1 - Current Ratings Characteristics

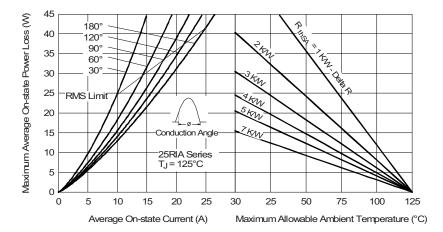


Fig. 2 - On-State Power Loss Characteristics

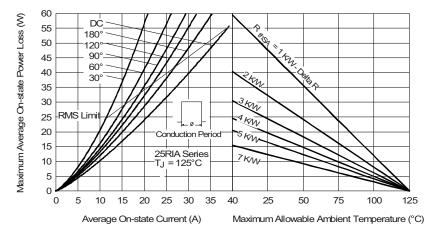


Fig. 3 - On-State Power Loss Characteristics

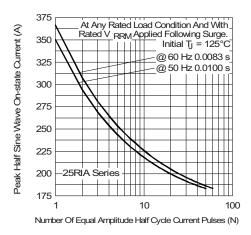


Fig. 4 - Maximum Non-Repetitive Surge Current

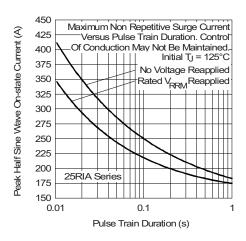


Fig. 5 - Maximum Non-Repetitive Surge Current

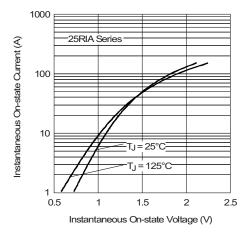


Fig. 6 - Forward Voltage Drop Characteristics

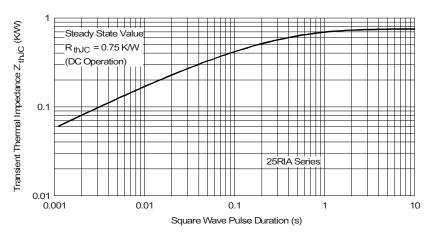


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics

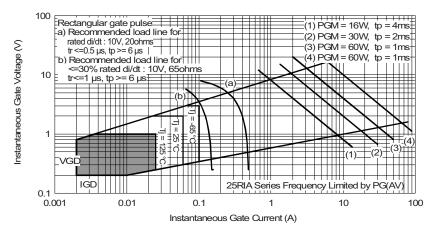
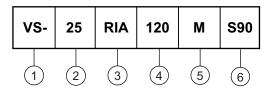


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



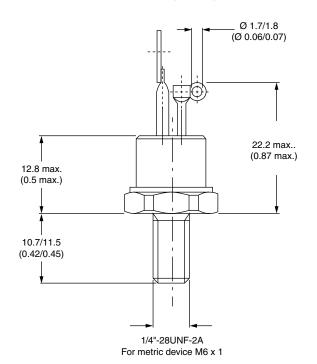
- Vishay Semiconductors product
- 2 Current code
- 3 Essential part number
- Voltage code x 10 = V_{RRM} (see Voltage Ratings table)
- None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A
 M = stud base TO-48 (TO-208AA) M6 x 1
- Critical dV/dt:
 None = 300 V/µs (standard value)
 S90 = 1000 V/µs (special selection)

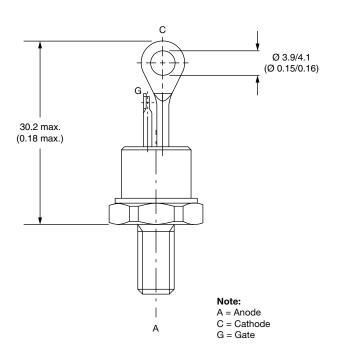
LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95333		

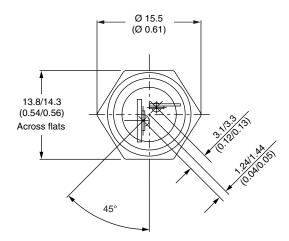


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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